# 1 GHz, 22 dB gain GaAs high output power doublerRev. 01 — 21 September 2009Product

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

#### 1.2 Features

- Excellent linearity
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant to Directive 2002/95/EC, regarding Restriction of the use of certain Hazardous Substances (RoHS)
- Integrated ring wave surge protection

#### 1.3 Applications

CATV systems operating in the 40 MHz to 1003 MHz frequency range

#### 1.4 Quick reference data

#### **Quick reference data** Table 1.

Bandwidth 40 MHz to 1003 MHz;  $V_B = 24 V (DC)$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \circ C$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz	-	21.5	-	dB
		f = 1003 MHz	22	22.7	23.5	dB
СТВ	composite triple beat	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	<u>[1]</u> _	-75	-65	dBc
CCN	carrier-to-composite noise	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	<u>[1]</u> 57	63	-	dBc
I <sub>tot</sub>	total current		[2] _	440	460	mA

[1] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

[2] Direct Current (DC).



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### 2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	input	
2, 3	common	
5	+V <sub>B</sub>	
7, 8	common	
9	output	2 3 7 8 sym095

### 3. Ordering information

Table 3. Orde	ering info	ormation			
Type number	Packag	age			
	Name	Description	Version		
CGD1042HI	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J		

#### 4. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
VB	supply voltage			-	30	V
V <sub>i(RF)</sub>	RF input voltage	single tone		-	75	dBmV
$V_{ESD}$	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	<u>[1]</u>	-	2000	V
		Biased; According IEC61000-4-2		-	1500	V
T <sub>stg</sub>	storage temperature			-40	+100	°C
T <sub>mb</sub>	mounting base temperature			-20	+100	°C

[1] The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

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#### 5. Characteristics

#### Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz;  $V_B = 24 V (DC)$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 °C$ ; unless otherwise specified.

	, D (			'			
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
G <sub>p</sub>	power gain	f = 50 MHz		-	21.5	-	dB
		f = 1003 MHz		22	22.7	23.5	dB
SL <sub>sl</sub>	slope straight line	f = 40 MHz to 1003 MHz	[1]	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	1	dB
RL <sub>in</sub>	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
RL <sub>out</sub>	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
		f = 870 MHz to 1003 MHz		17	-	-	dB
NF	noise figure	f = 50 MHz		-	4.6	5.6	dB
		f = 1003 MHz		-	5.5	6.5	dB
I <sub>tot</sub>	total current		[3]	-	440	460	mA
<b>79 NTSC</b>	channels + 75 digital channels						
СТВ	composite triple beat	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	-	-75	-65	dBc
CSO	composite second-order distortion	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	-	-77	-65	dBc
Xmod	cross modulation	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[4]	-	-68	-	dB
CCN	carrier-to-composite noise	V <sub>o</sub> = 56.4 dBmV at 1003 MHz	[4]	57	63	-	dBc
79 NTSC channels							
СТВ	composite triple beat	V <sub>o</sub> = 58.4 dBmV at 1003 MHz	[5]	-	-70	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 58.4 dBmV at 1003 MHz	[5]	-	-75	-	dBc
Xmod	cross modulation	V <sub>o</sub> = 58.4 dBmV at 1003 MHz	[5]	-	-65	-	dB

[1]  $G_p$  at 1003 MHz minus  $G_p$  at 40 MHz.

[2] Flatness is defined as peak deviation to straight line.

[3] Direct Current (DC).

[4] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

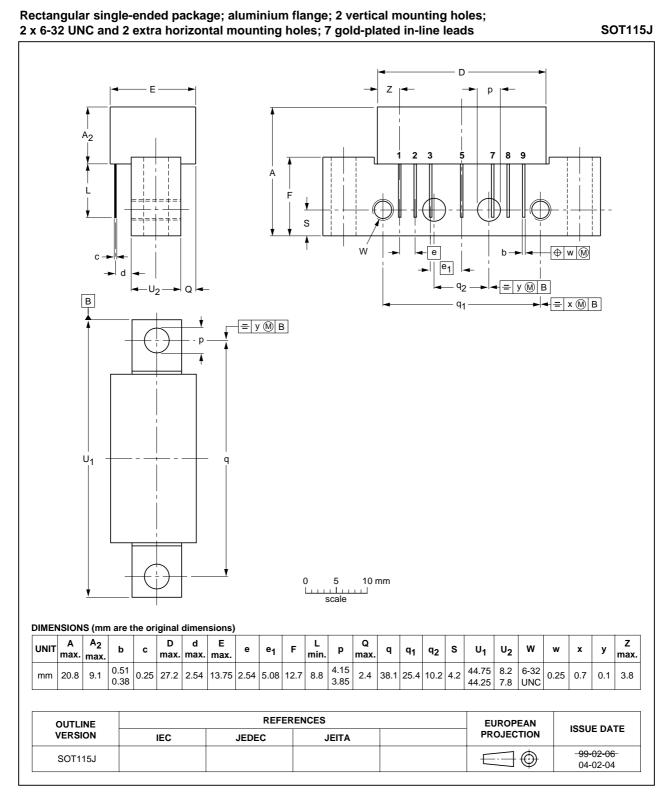
[5] 79 NTSC channels [f = 54 MHz to 550 MHz]; tilt extrapolated to 13.5 dB at 1003 MHz.

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## CGD1042HI

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#### 6. Package outline



#### Fig 1.Package outline SOT115J

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### 7. Abbreviations

Table 6.	Abbreviations
Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
RF	Radio Frequency
UNC	UNified Coarse

### 8. Revision history

Table 7. Revisi	on history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD1042HI_1	20090921	Product data sheet	-	-

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#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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**Product data sheet** 

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### CGD1042HI

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